

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	25301	"floating gate"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 11:32
L2	81	(trench or grooves) same ("pad oxide" or "gate oxide") same polysilicon same "hard mask"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 12:04
L3	780	(trench or grooves) and ("pad oxide" or "gate oxide") and polysilicon and "hard mask"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 12:04
L4	105	1 and 3	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 12:04
L9	96	8 and 1	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:03
L10	51	"poly oxide" same "silicon oxide"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:05
L11	12	10 and 1	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:03
L12	1098	(STI or "shallow trench isolation") and ("pad oxide" or "gate oxide") and polysilicon and ("SiN" or "etch stop" or "silicon nitride") and (CMP or "chemical mechanical polishing")	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:15
L13	219	1 and 12	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:14
L14	1323	(STI or "shallow trench isolation") and ("pad oxide" or "gate oxide" or oxidation or oxidizing) and polysilicon and ("SiN" or "etch stop" or "silicon nitride") and ("dry etch" or plasma)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:16
L15	1029	14 and "438"/\$.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:17

L16	160	15 and 1	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:17
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